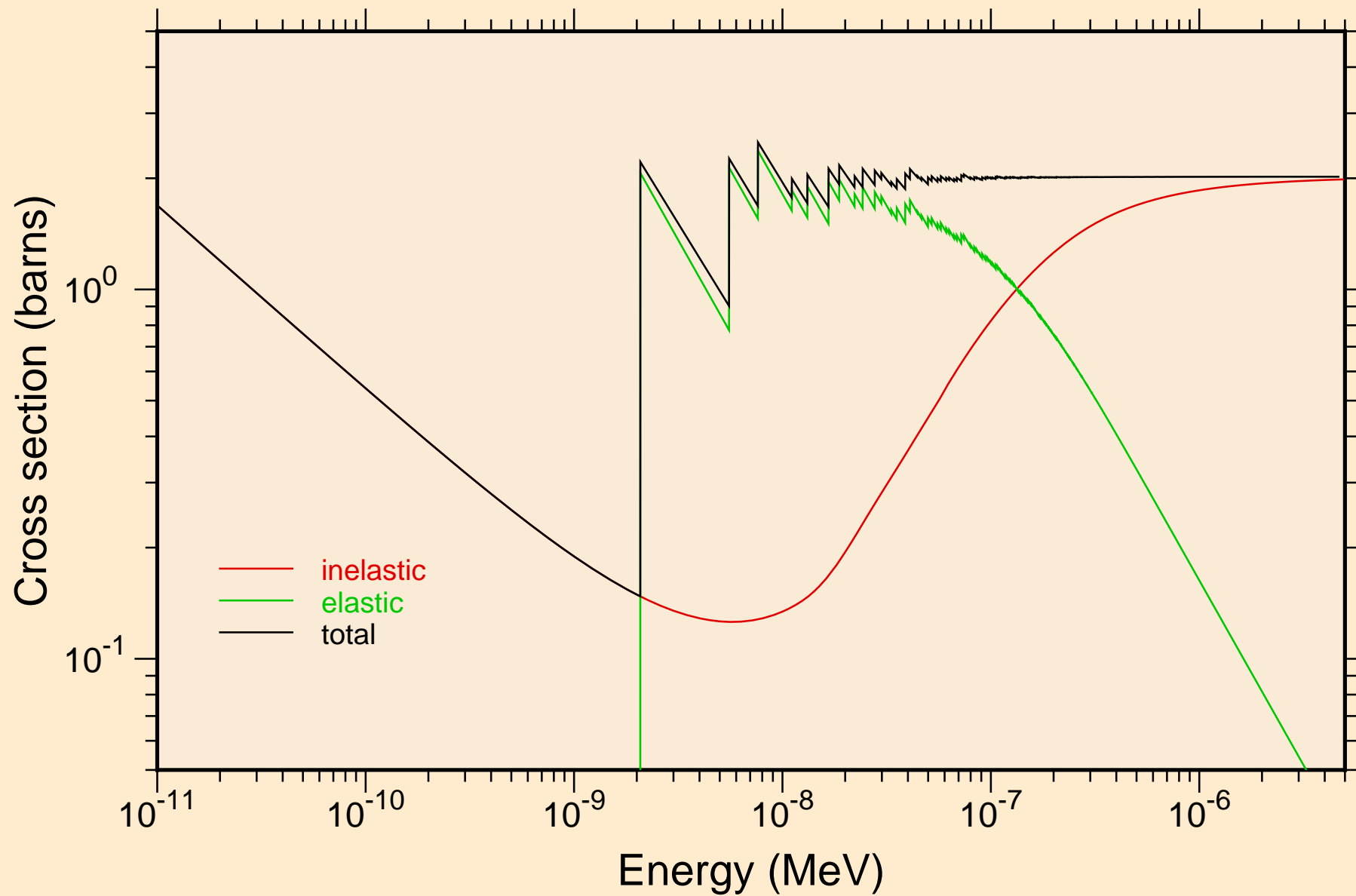
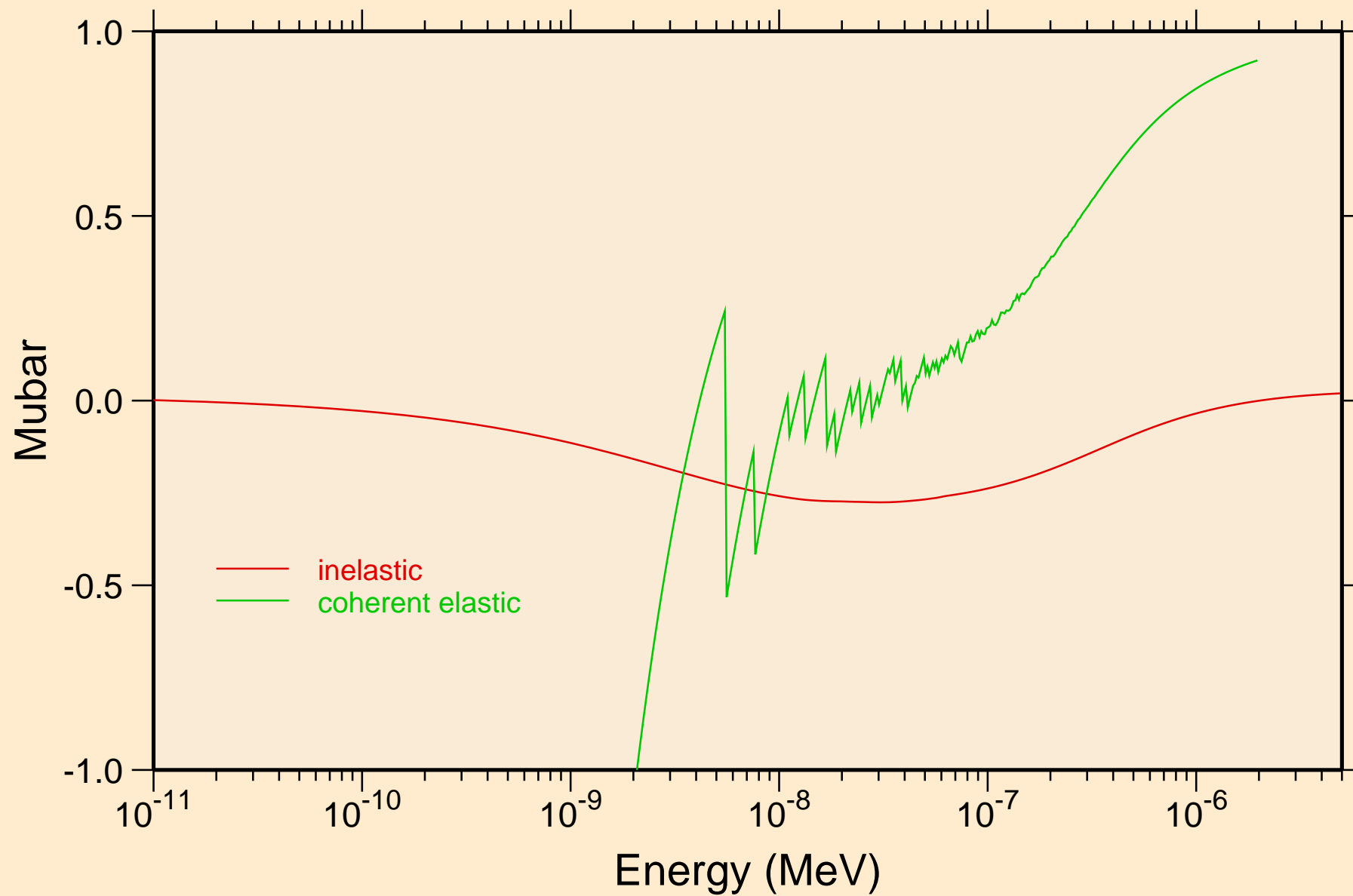


SI-SI_SG227_SILICON @ 293.60K

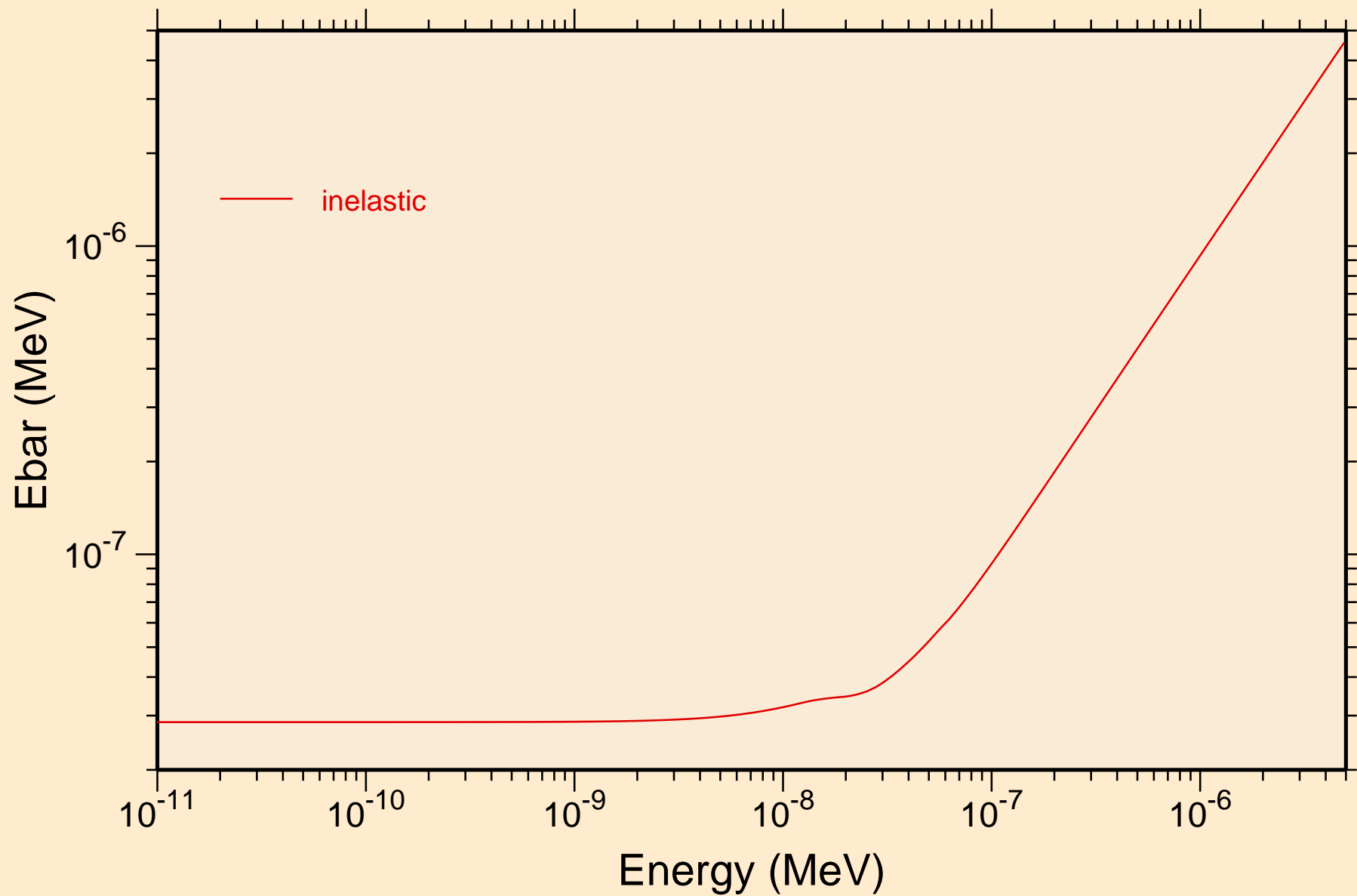
Thermal cross sections



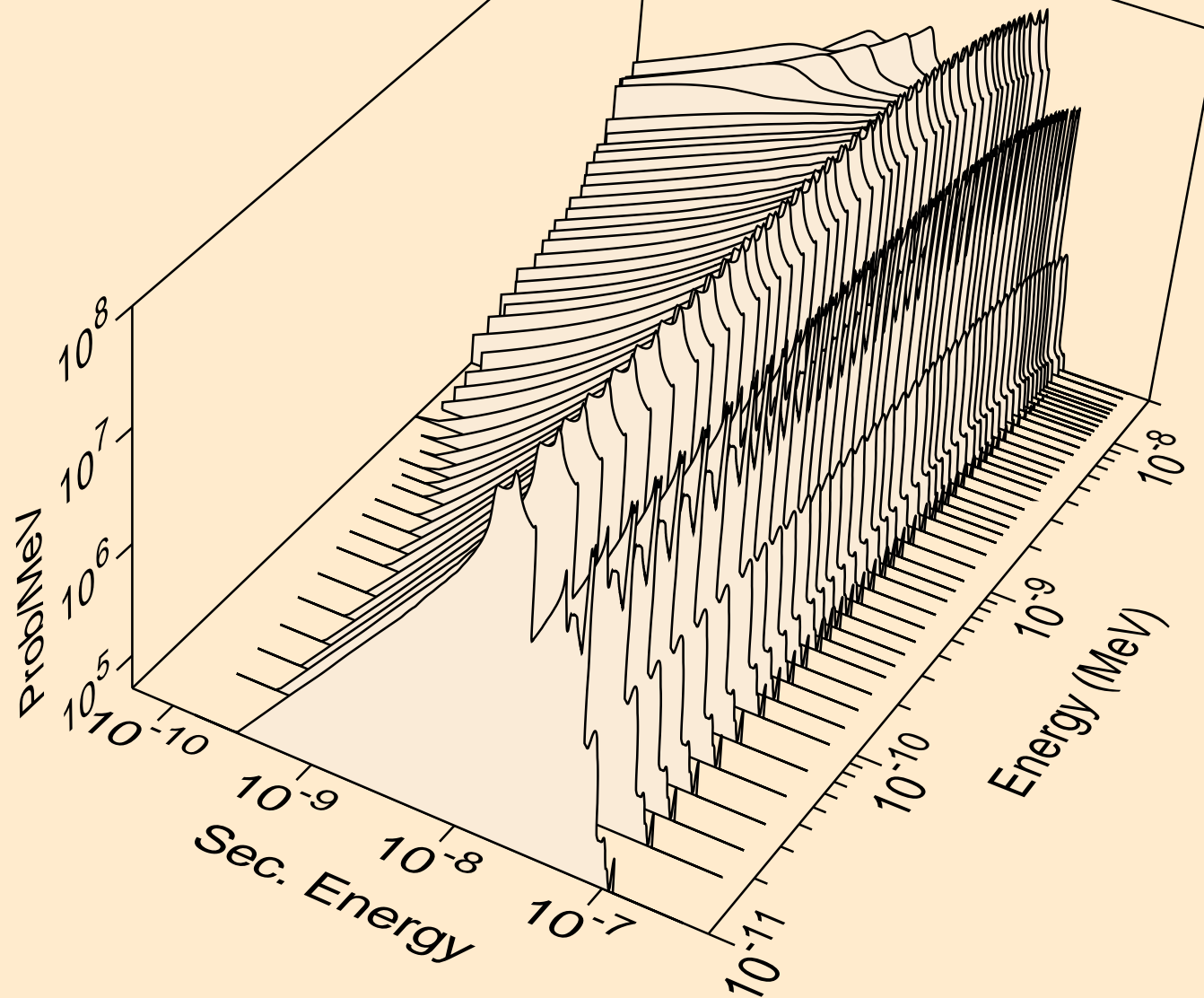
SI-SI_SG227_SILICON @ 293.60K
Thermal mubar



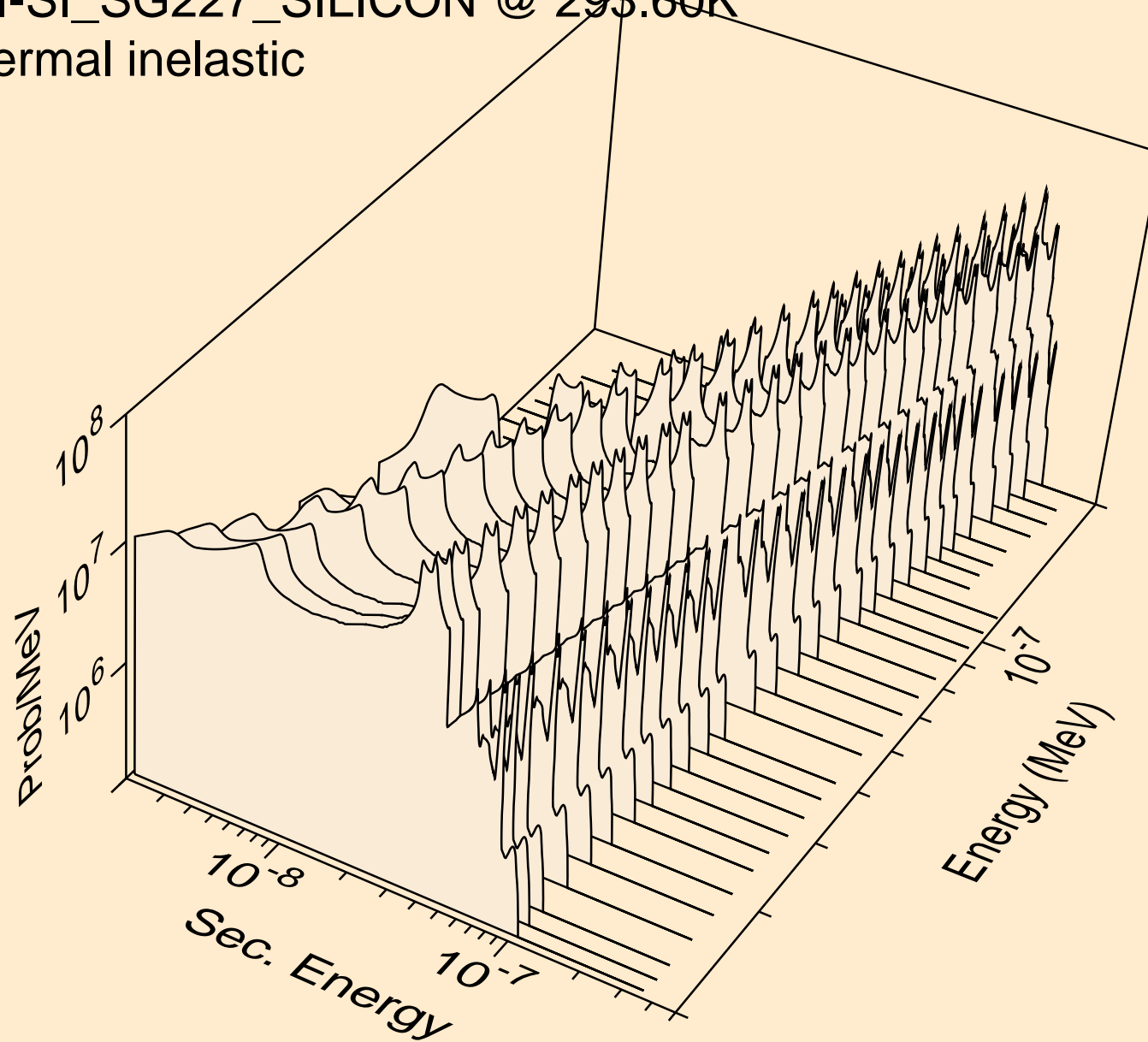
SI-SI_SG227_SILICON @ 293.60K
Thermal ebar



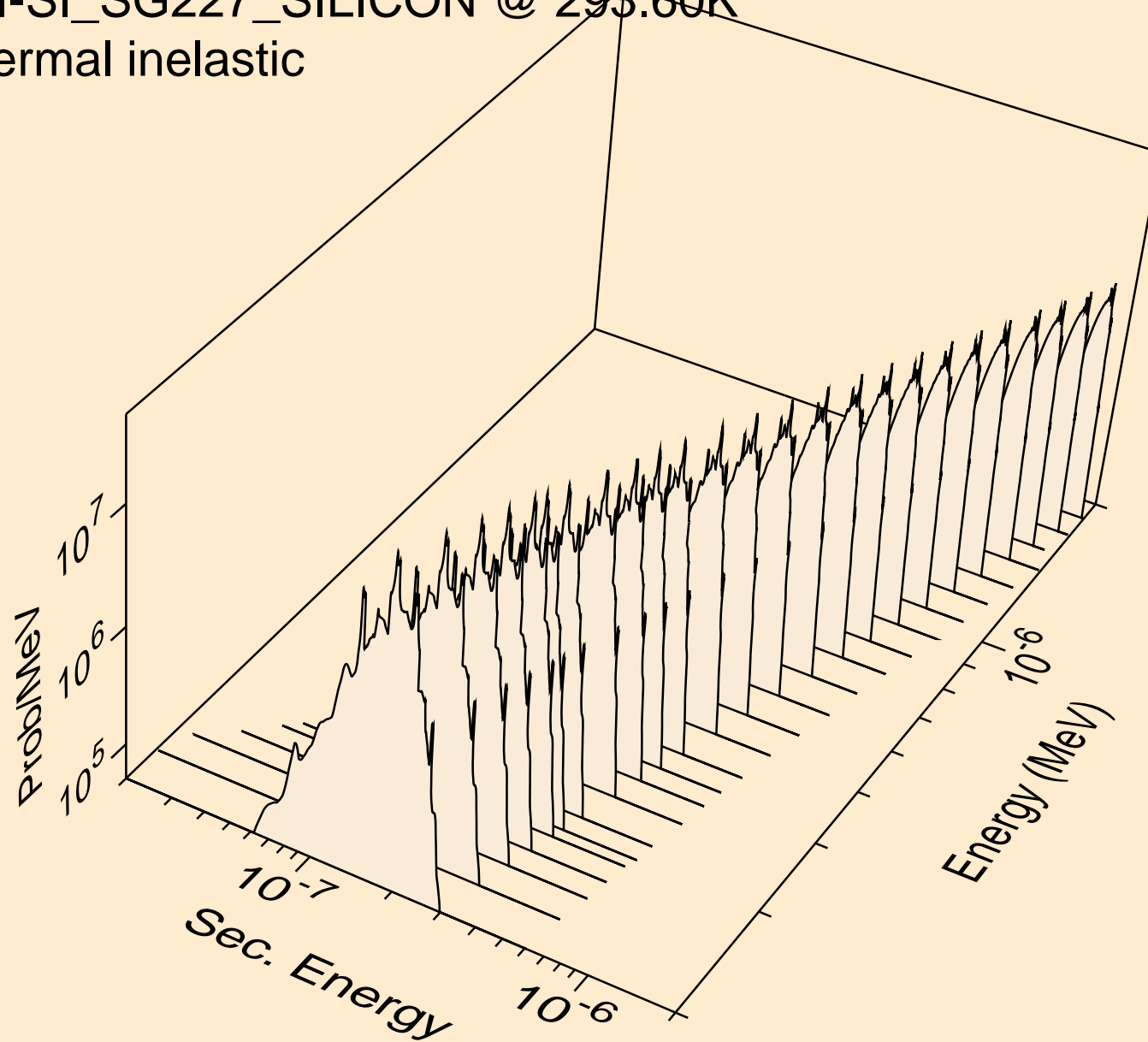
SI-SI_SG227_SILICON @ 293.60K
thermal inelastic



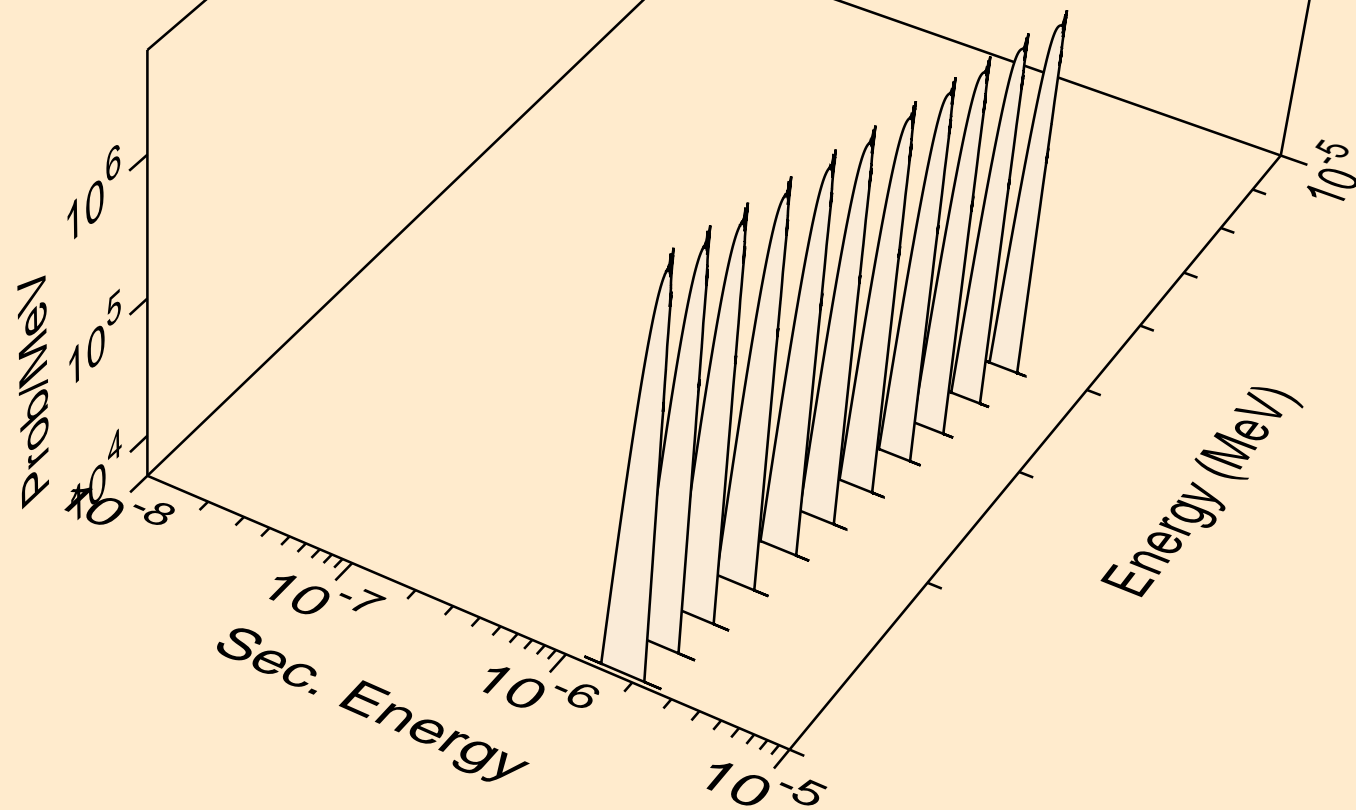
SI-SI_SG227_SILICON @ 293.60K
thermal inelastic



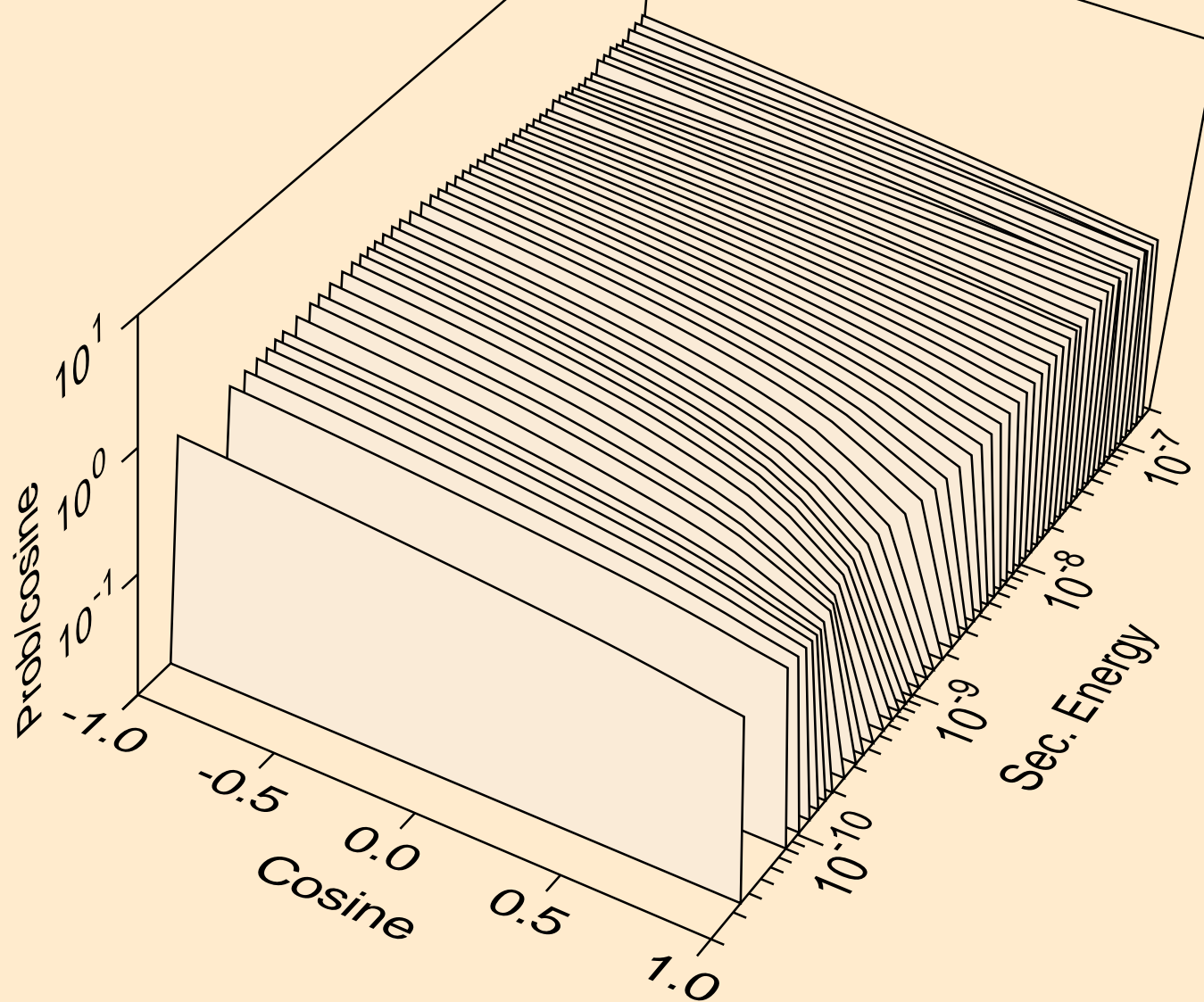
SI-SI_SG227_SILICON @ 293.60K
thermal inelastic



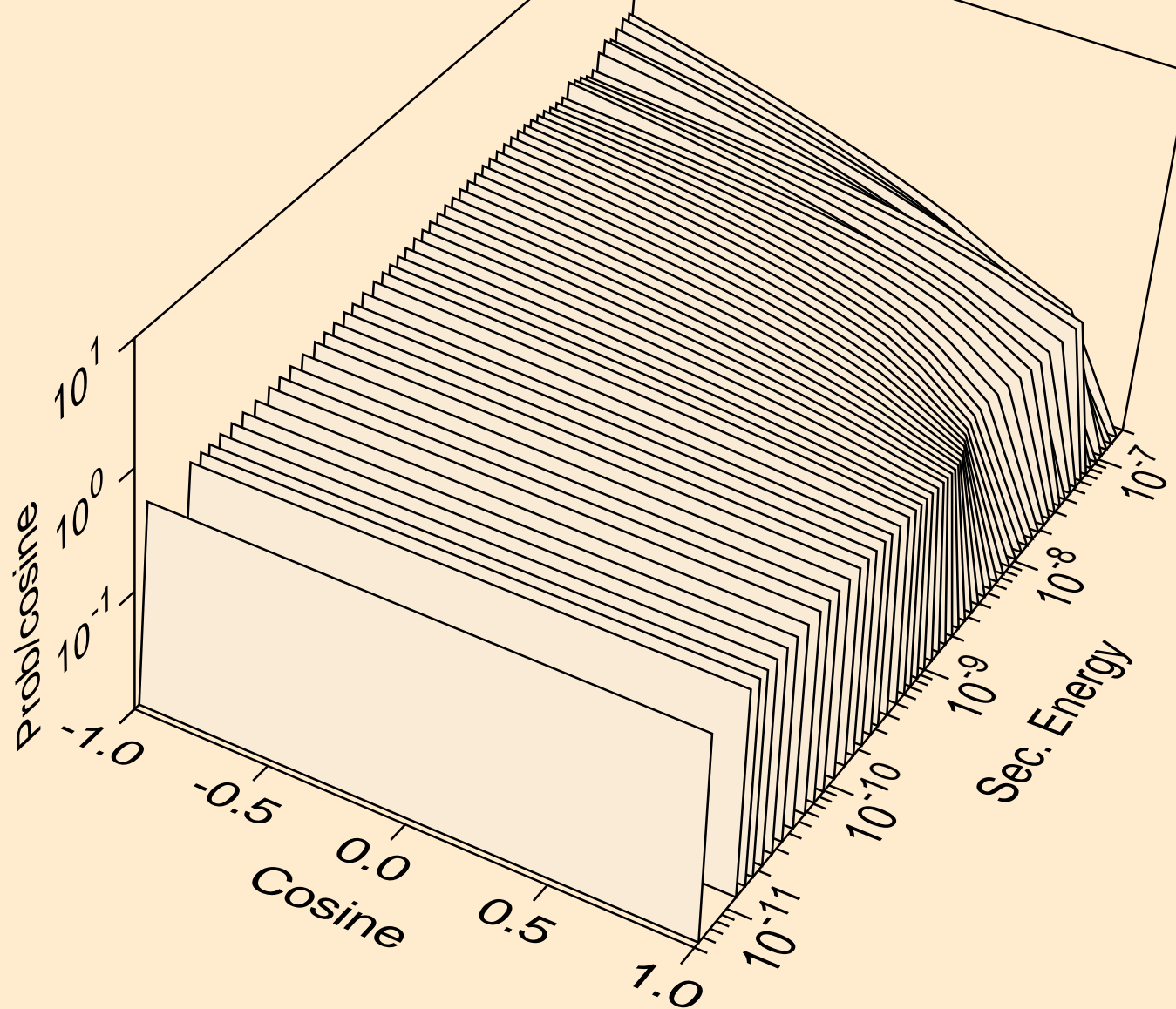
SI-SI_SG227_SILICON @ 293.60K
thermal inelastic



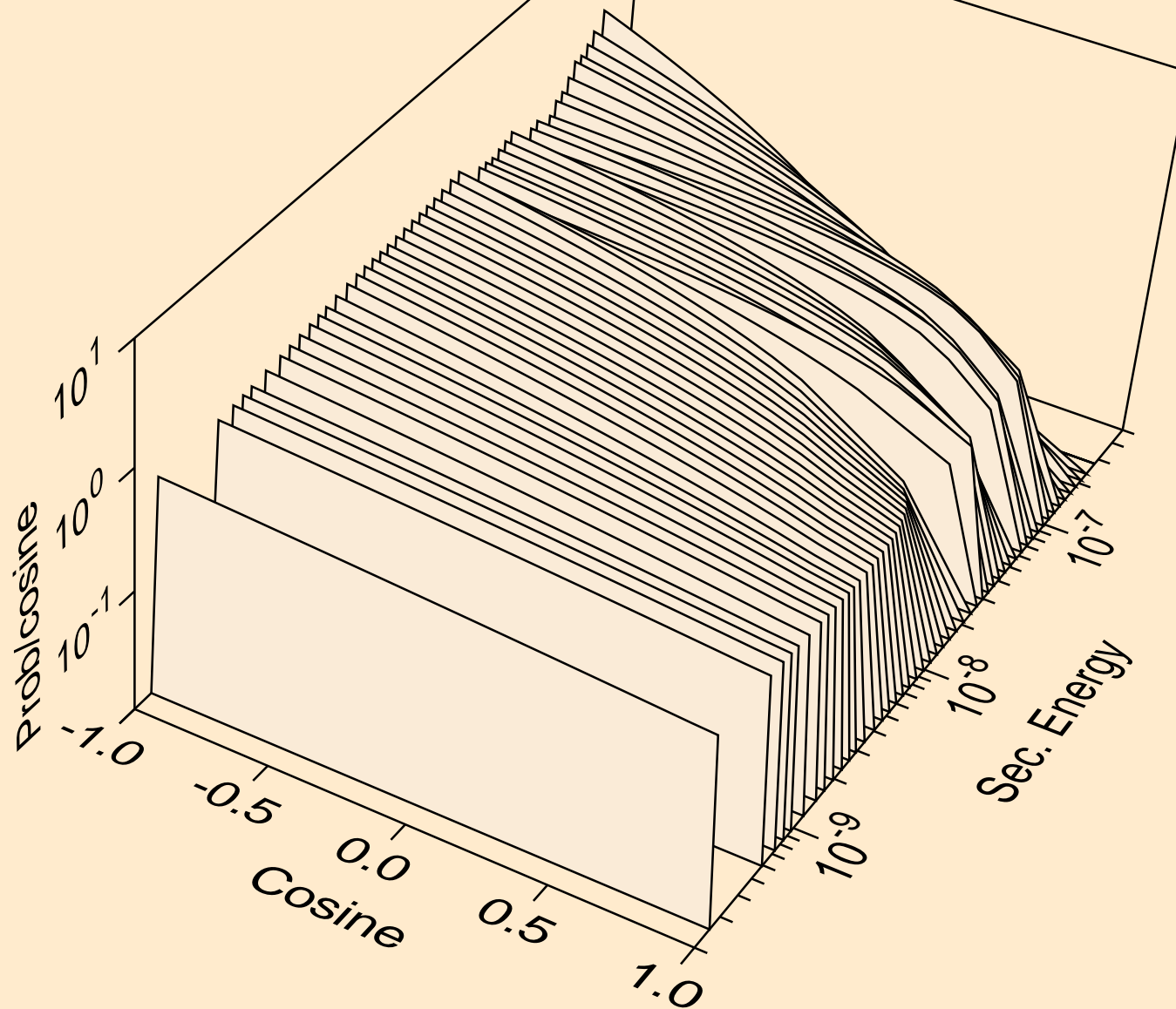
SI-SI_SG227_SILICON @ 293.60K
thermal inelastic for e= 1.012E-09 MeV



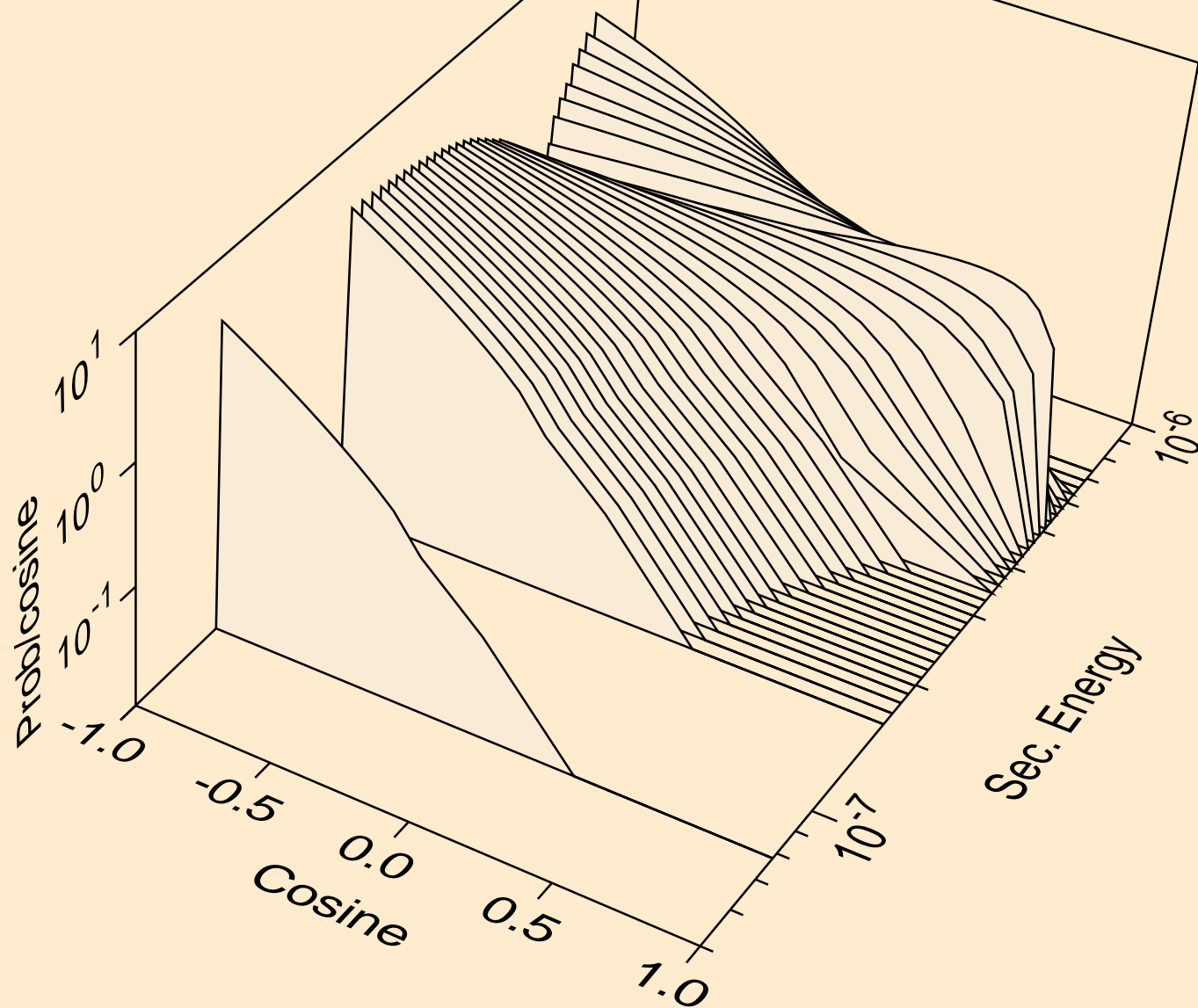
SI-SI_SG227_SILICON @ 293.60K
thermal inelastic for e= 1.417E-08 MeV



SI-SI_SG227_SILICON @ 293.60K
thermal inelastic for e= 9.000E-08 MeV



SI-SI_SG227_SILICON @ 293.60K
thermal inelastic for $e = 5.033\text{E-}07$ MeV



SI-SI_SG227_SILICON @ 293.60K
thermal inelastic for $e = 4.070\text{E-}06$ MeV

